

# Change of the electronic states in $\text{CeIn}_3$ , $\text{CeRhIn}_5$ and $\text{CePt}_3\text{Si}$ tuned by pressure

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## Abstract

We have studied a change of the electronic states in antiferromagnets  $\text{CeIn}_3$ ,  $\text{CeRhIn}_5$  and  $\text{CePt}_3\text{Si}$  via the de Haas–van Alphen experiments. The critical pressure  $P_c$ , where the Néel temperature becomes zero, is  $P_c \simeq 2.5$  GPa in  $\text{CeIn}_3$  with the cubic crystal structure, in which the narrow pressure region superconductivity appears below a superconducting transition temperature  $T_{sc} = 0.2$  K. In the pressure region  $P > P_c$ , we detected a main Fermi surface with the cyclotron mass  $m_c^* = 53m_0$ , which most likely corresponds to a nearly spherical Fermi surface in the paramagnetic state, namely a 4f-itinerant Fermi surface. The Fermi surface in the antiferromagnet  $\text{CeRhIn}_5$  with the tetragonal crystal structure is similar to that of  $\text{LaRhIn}_5$ , consisting of two kinds of nearly cylindrical Fermi surfaces. We observed a drastic change of the Fermi surface from 4f-localized ( $\text{LaRhIn}_5$ ) to 4f-itinerant ( $\text{CeCoIn}_5$ ) Fermi surfaces at  $P_c \simeq 2.4$  GPa. The cyclotron mass increases intensively above 1.6 GPa where superconductivity sets in.  $\text{CePt}_3\text{Si}$  with the tetragonal crystal structure without inversion symmetry is highly different from  $\text{CeIn}_3$  and  $\text{CeRhIn}_5$  in magnetism and superconductivity. It orders antiferromagnetically below  $T_N = 2.3$  K and becomes superconductive below  $T_{sc} = 0.6$  K at ambient pressure. With increasing pressure, the cyclotron mass is found to be reduced, together with a steep decrease of  $T_N$  and  $T_{sc}$ , where  $P_c$  is most likely about 1.5 GPa in  $\text{CePt}_3\text{Si}$ . The heavy fermion state of  $\text{CePt}_3\text{Si}$  is realized at ambient pressure.  
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## 1. Introduction

The 4f electron of cerium compounds exhibits a variety of characteristic features including magnetic and charge orderings, spin and valence fluctuations, heavy fermions and anisotropic superconductivity. The electronic states in the cerium compounds, where the Ruderman–Kittel–Kasuya–Yosida (RKKY) interaction and the Kondo effect compete each other, can be tuned by pressure. When pressure  $P$  is applied to the cerium compounds with antiferromagnetic ordering such as  $\text{CeIn}_3$  and  $\text{CeRhIn}_5$ , the Néel temperature  $T_N$  decreases, and a quantum critical point corresponding to the extrapolation  $T_N \rightarrow 0$  is reached at  $P = P_c$  [1–4]. Surprisingly, superconductivity and/or the non-Fermi liquid nature

appear around  $P_c$ . Crossover from the magnetically ordered state to the non-magnetic state under pressure is currently the most interesting issue in the cerium compounds.

We have studied a change of the electronic states in antiferromagnets  $\text{CeIn}_3$ ,  $\text{CeRhIn}_5$  and  $\text{CePt}_3\text{Si}$  via the de Haas–van Alphen (dHvA) experiments under pressure. The electronic states, which are tuned by pressure, have been investigated via challenging dHvA experiments. The present paper reports the dHvA results at high pressures up to 3 GPa, indicating a drastic change of the Fermi surface properties. A relation between superconductivity and the Fermi surface properties has been also investigated.

## 2. Experimental

Single crystals were grown by the Czochralski pulling method in an rf-furnace for  $\text{CeIn}_3$ , the In-flux method for

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CeRhIn<sub>5</sub>, and the Bridgeman method and mineralization for CePt<sub>3</sub>Si [5–7]. The residual resistivity ratio RRR ( $=\rho_{RT}/\rho_0$ ,  $\rho_{RT}$  is the electrical resistivity at room temperature,  $\rho_0$  is the residual resistivity) is 90 in CeIn<sub>3</sub>, 330 in CeRhIn<sub>5</sub> and 106 in CePt<sub>3</sub>Si, indicating high-quality samples.

The dHvA experiments were done by the standard field modulation method with a modulation frequency of 3.5 Hz and a modulation field of 80 Oe. Pressure was applied by utilizing an MP35N piston cylinder cell with a 1:1 mixture of commercial Daphne oil (7373) and kelosene, and calibrated by the superconducting transition temperature of Sn.

### 3. Experimental results and discussion

#### 3.1. CeIn<sub>3</sub>

CeIn<sub>3</sub> with the AuCu<sub>3</sub>-type cubic crystal structure is a well-known Kondo-lattice compound with antiferromagnetic ordering at 10 K. With increasing pressure, the Néel temperature decreases and becomes zero around 2.5 GPa. The critical pressure is  $P_c \simeq 2.5$  GPa, in which the narrow pressure region superconductivity appears below  $T_{sc}=0.2$  K [1,3].

We carried out the dHvA experiment under pressure. The detected dHvA signal  $V_{osc}$  for the magnetic field  $H$  is simply written as follows:

$$V_{osc} = A \sin \left( \frac{2\pi F}{H} + \phi \right),$$

where the dHvA frequency  $F$  ( $=\hbar S_F/2\pi e$ ), which is expressed as a unit of magnetic field, corresponds to the extremal (maximum or minimum) cross-sectional area of the Fermi surface  $S_F$ . From the temperature dependence of the dHvA amplitude  $A$ , we can determine the cyclotron effective mass  $m_c^*$ .

Figs. 1 and 2 show the pressure dependence of dHvA frequency  $F$  and cyclotron mass  $m_c^*$  for the magnetic field  $H$  along  $\langle 110 \rangle$ . The dHvA frequency for branch “d” increases slightly with increasing pressure. The similar pressure dependence of the cyclotron mass is also observed:  $m_c^* = 17m_0$  at ambient pressure, and  $20m_0$  at 2.4 GPa for branch “d”. In-

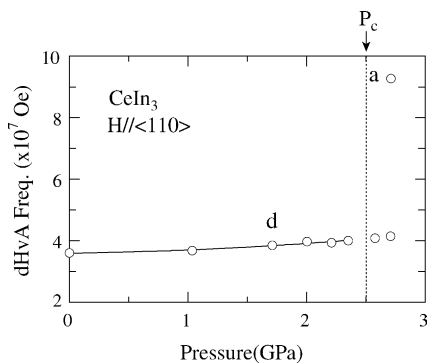


Fig. 1. Pressure dependence of the dHvA frequency in CeIn<sub>3</sub>.

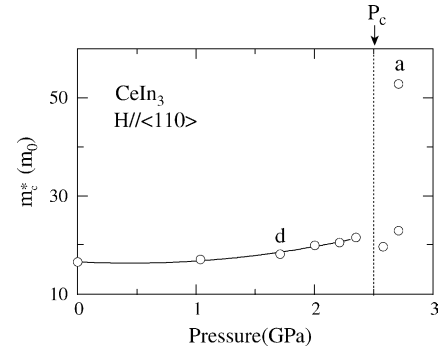


Fig. 2. Pressure dependence of the cyclotron mass in CeIn<sub>3</sub>.

teresting is that branch “a”, which is observed at 2.7 GPa, possesses an extremely large cyclotron mass  $m_c^* = 53m_0$ . Branch “a” is the main Fermi surface, which is not observed below  $P_c \simeq 2.5$  GPa. An appearance of branch “a” indicates that CeIn<sub>3</sub> becomes paramagnetic.

To clarify the origin of the dHvA branches, we show in Fig. 3 the Fermi surface in LaIn<sub>3</sub>, which was calculated by the FLAPW method. The Fermi surface consists of a complicated band 6 hole-Fermi surface and a nearly spherical band 7 electron-Fermi surface. The former Fermi surface consists of three kinds of major parts, which are centered at  $\Gamma$ , R and X points. Among them, a Fermi surface centered at  $\Gamma$ , denoted by “d”, is electron in dispersion and is spherical in topology, bulges slightly along  $\langle 100 \rangle$  and possesses a slender arm along  $\langle 111 \rangle$ .

As discussed in Refs. [5,8], the Fermi surface of CeIn<sub>3</sub> at ambient pressure is approximately similar to that of LaIn<sub>3</sub>, although it is strongly modified by the magnetic Brillouin zone boundaries. The dHvA frequency of branch “d”, observed experimentally in the whole angle region, is in good agreement with the theoretical branch “d” of LaIn<sub>3</sub> in magnitude, although branch “d” in CeIn<sub>3</sub> corresponds to a nearly spherical Fermi surface, not possessing the slender arm along  $\langle 111 \rangle$  as in LaIn<sub>3</sub> and is slightly large in volume of the Fermi surface compared to LaIn<sub>3</sub>. In the case of LuIn<sub>3</sub>, the topology of the corresponding Fermi surface is nearly spherical, possessing no arms. This Fermi surface corresponds to branch “d” of CeIn<sub>3</sub>.

A spherical electron Fermi surface in band 7, denoted by “a” in LaIn<sub>3</sub>, is not observed at ambient pressure in CeIn<sub>3</sub>,

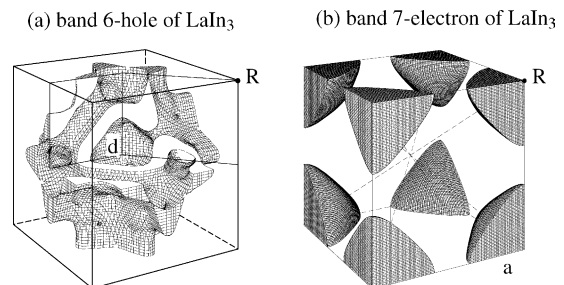


Fig. 3. Theoretical Fermi surfaces in LaIn<sub>3</sub>.

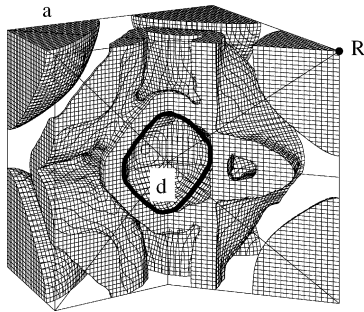


Fig. 4. Band 7 electron-Fermi surface in  $\text{CeIn}_3$ , calculated on the basis of the 4f-itinerant band model.

which is ascribed to the influence of the magnetic Brillouin zone boundaries. A large spherical Fermi surface named “a” also exists in the case where the 4f electron in  $\text{CeIn}_3$  becomes itinerant. Fig. 4 shows the band 7 electron-Fermi surface based on the 4f-itinerant band model [9]. The theoretical dHvA frequency of branch “a” is  $F = 6.84 \times 10^7$  Oe for  $\text{LaIn}_3$ , while it is  $8.50 \times 10^7$  Oe for the 4f-itinerant band model for  $H \parallel \langle 110 \rangle$ . The detected dHvA frequency of  $9.34 \times 10^7$  Oe is close to the itinerant one.

For branch “d”, similar values for experiment and theory are found as well. The theoretical dHvA frequency for  $\text{LaIn}_3$  is  $F = 2.54 \times 10^7$  Oe for  $\langle 100 \rangle$  and  $2.29 \times 10^7$  Oe for  $\langle 111 \rangle$ , while  $F = 2.20 \times 10^7$  Oe for  $\langle 100 \rangle$ ,  $2.38 \times 10^7$  Oe for  $\langle 110 \rangle$  and  $2.11 \times 10^7$  Oe for  $\langle 111 \rangle$  for the 4f-itinerant band model. This is a reason why a change of the dHvA frequency of branch “d” is not observed clearly above and below  $P_c$ :  $3.59 \times 10^7$  Oe at 0 GPa,  $3.97 \times 10^7$  Oe at 2.0 GPa and  $4.19 \times 10^7$  Oe at 2.7 GPa for branch “d” for  $\langle 110 \rangle$  experimentally.

From these experimental results, it is concluded that a change of the Fermi surface from 4f-localized to 4f-itinerant occurs when pressure crosses  $P_c \simeq 2.5$  GPa. Superconductivity appears in a narrow pressure region  $\Delta P_c \simeq 0.5$  GPa around  $P_c$ . From the NQR experiment, it is clarified that a pressure-induced phase separation of antiferromagnetism and paramagnetism occurs and superconductivity coexists with antiferromagnetism in the pressure region from 2.28 to 2.5 GPa [3]. On the other hand, superconductivity is also realized in the paramagnetic state above  $P_c \simeq 2.5$  GPa, following the Fermi liquid relation.

### 3.2. $\text{CeRhIn}_5$

$\text{CeTIn}_5$  (T: Co, Rh and Ir) crystallizes in the tetragonal crystal structure. The uniaxially distorted  $\text{AuCu}_3$ -type layers of  $\text{CeIn}_3$  and the  $\text{TIn}_2$  layers are stacked sequentially along the  $[001]$  direction ( $c$ -axis).  $\text{CeCoIn}_5$  and  $\text{CeIrIn}_5$  reveal superconductivity at ambient pressure [10], whereas  $\text{CeRhIn}_5$  orders antiferromagnetically below  $T_N=3.8$  K [2,11,12]. With increasing pressure, the Néel temperature in  $\text{CeRhIn}_5$  increases, has a maximum around 1 GPa, and decreases with further increasing pressure. A smooth extrapolation indicates

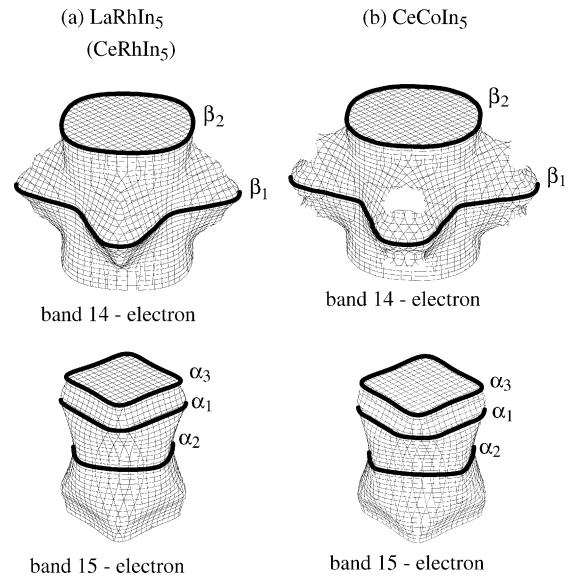


Fig. 5. Theoretical Fermi surfaces in (a)  $\text{LaRhIn}_5$  ( $\text{CeRhIn}_5$ ) and (b)  $\text{CeCoIn}_5$ . Small Fermi surfaces are not shown.

$T_N \rightarrow 0$  around a pressure  $P = 2.3\text{--}2.5$  GPa.  $\text{CeRhIn}_5$ , however, reveals superconductivity in a wide pressure region from  $P^* = 1.6\text{--}5.2$  GPa. Its transition temperature has a maximum around 2.3–2.5 GPa, with  $T_{sc}=2.2$  K. This pressure of 2.3–2.5 GPa is supposed to be a critical pressure  $P_c$  in  $\text{CeRhIn}_5$ , where the antiferromagnetic state is changed into a paramagnetic state and also the heavy fermion state is most likely realized in this compound.

The topology of main Fermi surfaces in the antiferromagnet  $\text{CeRhIn}_5$  is nearly cylindrical, and is found to be approximately the same as that of a non-4f reference compound  $\text{LaRhIn}_5$ , as shown in Fig. 5(a), indicating that the 4f electron in  $\text{CeRhIn}_5$  is localized and does not contribute to the volume of the Fermi surfaces [6]. On the other hand, main Fermi surfaces in  $\text{CeCoIn}_5$  without magnetic ordering are also nearly cylindrical but are identified by the 4f-itinerant band model, as shown in Fig. 5(b) [6,13]. The topology of the two kinds of cylindrical Fermi surfaces of  $\text{CeCoIn}_5$  is similar to that of  $\text{CeRhIn}_5$ , but one 4f-electron in each Ce site becomes a conduction electron in  $\text{CeCoIn}_5$ . The detected cyclotron masses of  $5\text{--}87m_0$  in  $\text{CeCoIn}_5$  are extremely large, reflecting a large  $\gamma$  value of  $1000$  mJ/K<sup>2</sup> mol [10,13,14]. It is noted that the “d” electrons in the T atom hybridize with the 5p electrons of In in  $\text{CeTIn}_5$  and also  $\text{LaTIn}_5$ , which results in a small density of states around the Fermi energy. This means that there are very few conduction electrons in the  $\text{TIn}_2$  layer and hence the Fermi surface mainly consists of the two kinds of cylindrical Fermi surfaces shown in Fig. 5.

To elucidate a change of the Fermi surface properties under pressure, we show in Figs. 6 and 7 the pressure dependence of the dHvA frequency and the cyclotron mass, respectively. The dHvA frequencies for the main dHvA branches named  $\beta_2$ ,  $\alpha_1$  and  $\alpha_{2,3}$ , together with branches named a, b and c, in Fig. 6 are approximately unchanged up to about 2.3 GPa, as

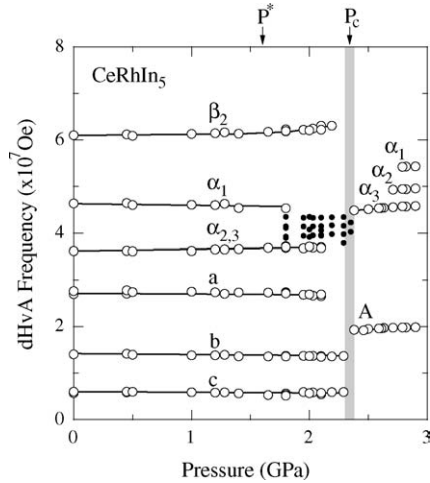


Fig. 6. Pressure dependence of the dHvA frequency in CeRhIn<sub>5</sub>.

reported previously, although the previous experiments were carried out up to 2.1 GPa [12]. These branches, however, disappear completely at 2.35 GPa, and another two branches with  $F = 4.23 \times 10^7$  Oe ( $m_c^* \simeq 30m_0$ ) and  $4.03 \times 10^7$  Oe ( $20m_0$ ) appear at 2.35 GPa. We note that these branches appear from 1.8 to 2.35 GPa, which are shown by small closed circles in Fig. 6. The origin of these branches are unknown.

Above 2.4 GPa, new dHvA branches named  $\alpha_i$  ( $i = 1-3$ ) and A appear:  $F = 5.43 \times 10^7$  Oe ( $m_c^* = 23m_0$ ) in  $\alpha_1$ ,  $4.96 \times 10^7$  Oe ( $30m_0$ ) in  $\alpha_2$ ,  $4.58 \times 10^7$  Oe ( $24m_0$ ) in  $\alpha_3$  and  $1.98 \times 10^7$  Oe ( $9m_0$ ) in branch A at 2.9 GPa. The dHvA frequencies of branches  $\alpha_i$  are larger than those below 2.4 GPa, but are approximately the same as those of CeCoIn<sub>5</sub> at ambient pressure:  $F = 5.56 \times 10^7$  Oe ( $m_c^* = 15m_0$ ) in  $\alpha_1$ ,  $4.53 \times 10^7$  Oe ( $18m_0$ ) in  $\alpha_2$  and  $4.24 \times 10^7$  Oe ( $8.4m_0$ ) in  $\alpha_3$  in CeCoIn<sub>5</sub>. The present dHvA data indicate that the 4f electron becomes itinerant and significantly contributes to the volume of the Fermi surface.

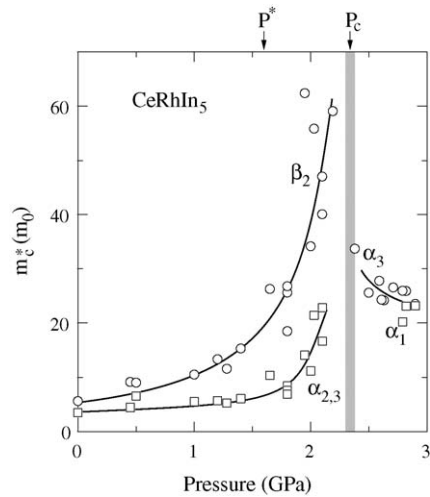


Fig. 7. Pressure dependence of the cyclotron mass in CeRhIn<sub>5</sub>.

As shown in Fig. 7, the cyclotron masses of main branches  $\beta_2$  and  $\alpha_{2,3}$  increase steeply above 1.6 GPa where superconductivity sets in:  $5.5m_0$  at ambient pressure,  $20m_0$  at 1.6 GPa and  $60m_0$  at 2.2 GPa for branches  $\beta_2$ , where the cyclotron mass was determined in the field range from 100 to 169 kOe, namely at an effective field  $H_{\text{eff}} = 126$  kOe. On the other hand, the cyclotron mass of the new branch  $\alpha_3$ , which was observed above 2.4 GPa, decreases slightly with increasing pressure: about  $30m_0$  at 2.4 GPa and  $24m_0$  at 2.9 GPa. Branch  $\beta_2$  was, however, not detected above 2.4 GPa. This is mainly due to a large cyclotron effective mass close to  $100m_0$ . We note that the cyclotron mass above 1.6 GPa, including the cyclotron mass in CeCoIn<sub>5</sub>, is field-dependent as described in Refs. [12,13].

From these experimental results, a critical pressure is determined as  $P_c \simeq 2.4$  GPa. The topology of the Fermi surface is thus found to be different between  $P < P_c$  ( $\simeq 2.4$  GPa) and  $P > P_c$ . Nevertheless superconductivity is observed in both the pressure regions ranging from 1.6 to 5.2 GPa [11,15]. From the NQR experiment at 1.75 GPa, superconductivity with a d-wave type is found to coexist with the antiferromagnetic state [16], and also from the neutron scattering experiment, the magnetic structure and the magnetic moment are almost unchanged up to 1.63 GPa [17]. It is important to emphasize that the cyclotron masses are extremely large in these pressure regions below  $P_c$  as well as above  $P_c$ , forming a heavy fermion state. We also note that the upper critical field  $H_{c2}$  in superconductivity and a slope of  $H_{c2}$  at  $T_c$ ,  $-dH_{c2}/dT$  at 2.5 GPa for the magnetic field along [001] ( $c$ -axis) are 100 kOe and 150 kOe/K, respectively [11], which are compared to 50 kOe and 110 kOe/K in CeCoIn<sub>5</sub> at ambient pressure [13]. This indicates that the electronic specific heat coefficient  $\gamma$  at 2.5 GPa in CeRhIn<sub>5</sub> is larger than  $\gamma = 1000$  mJ/K<sup>2</sup> mol in CeCoIn<sub>5</sub>.

### 3.3. CePt<sub>3</sub>Si

A recently discovered superconductor CePt<sub>3</sub>Si with the tetragonal crystal structure possesses unique characteristics [18]. Superconductivity with the transition temperature  $T_{\text{sc}} = 0.75$  K is realized in the long-range antiferromagnetic state with the Néel temperature  $T_{\text{N}} = 2.2$  K. This is in contrast with superconductivity in the previous cerium-based heavy fermion superconductors where superconductivity occurs in the nonmagnetic state or the antiferromagnetically spin-fluctuating state [19].

Moreover, it is noted that CePt<sub>3</sub>Si is the first heavy fermion superconductor lacking a center of symmetry in the tetragonal crystal structure. Very recently we have also observed superconductivity in the vicinity of a critical pressure for a ferromagnet UR without inversion symmetry where a Curie temperature becomes approximately zero [20]. The relation between superconductivity and lack of inversion symmetry is currently an interesting issue.

The topology of the Fermi surface in CePt<sub>3</sub>Si is most likely similar to that in LaPt<sub>3</sub>Si. In fact, one small Fermi surface



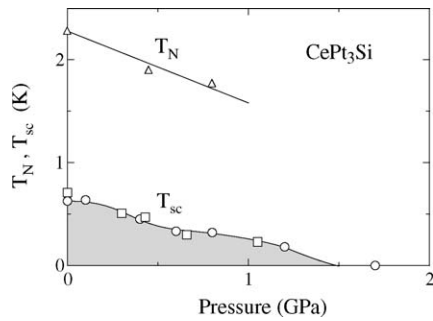


Fig. 8. Pressure dependence of the Néel temperature  $T_N$  and the superconducting transition temperature  $T_{sc}$  in  $\text{CePt}_3\text{Si}$ . The data shown by triangles and circles were obtained by the resistivity measurement, and those by squares are due to the ac-susceptibility one.

named  $\delta$  ( $F = 1.6 \times 10^7$  Oe and  $m_c^* = 2.9m_0$ ) in  $\text{CePt}_3\text{Si}$  is the same as that in  $\text{LaPt}_3\text{Si}$ , where the main Fermi surface in  $\text{LaPt}_3\text{Si}$  consists of three-dimensional multiply connected Fermi surfaces [21]. The much larger main Fermi surfaces are not detected experimentally, most likely due to the antiferromagnetic structure in  $\text{CePt}_3\text{Si}$  and the large cyclotron mass of the main Fermi surfaces based on the large electronic specific heat coefficient 300–400 mJ/K<sup>2</sup> mol [18].

We have also carried out the dHvA and electrical resistivity measurements under pressure in  $\text{CePt}_3\text{Si}$ . With increasing pressure, the Néel temperature  $T_N = 2.3$  K and the superconducting transition temperature  $T_{sc} \simeq 0.65$  K are found to decrease markedly, and become zero around 1.5 GPa, as shown in Fig. 8. The corresponding dHvA frequency of branch  $\delta$  slightly increases in magnitude, while the cyclotron effective mass decreases with increasing pressure:  $2.9m_0$  at 0 GPa and  $2.4m_0$  at 1.3 GPa. The critical pressure  $P_c$  is most likely 1.5 GPa. Above  $P_c = 1.5$  GPa another branch  $F = 2.20 \times 10^7$  Oe with  $m_c^* = 19m_0$  is observed whose cyclotron mass decreases steeply with further increasing pressure.

The heavy fermion state of  $\text{CePt}_3\text{Si}$  is most likely realized at ambient pressure even in the antiferromagnetic state, which is closely related to an appearance of superconductivity. In other words, applying pressure derives the electronic state away from the heavy fermion state and also superconductivity.

#### 4. Concluding remark

We have studied the Fermi surface properties of antiferromagnets  $\text{CeIn}_3$ ,  $\text{CeRhIn}_5$  and  $\text{CePt}_3\text{Si}$  via the dHvA experiments under pressure. The application of pressure to these compounds is useful to control the electronic states. The topology of the Fermi surface is found to be unchanged up to  $P_c$ , but an abrupt change of the Fermi surface is observed above  $P_c$  for the three compounds. The precise dHvA data are obtained in  $\text{CeRhIn}_5$ . When pressure approaches  $P_c$ , the cyclotron mass of the main Fermi surface in  $\text{CeRhIn}_5$  increases

steeply, indicating the heavy fermion state, and decreases considerably when the pressure deviates from  $P_c$ . Around  $P_c$ , the heavy fermion state is formed, although the topology of the Fermi surface is different between below and above  $P_c$ . Namely, the 4f electron is localized below  $P_c$ , while the 4f electron becomes itinerant above  $P_c$  and contributes to the volume of the Fermi surface. Superconductivity of  $\text{CeRhIn}_5$  is not related to the topology of the Fermi surface but is closely related to this heavy fermion state. It is also noted that quasi-two-dimensionality enhances the superconducting transition temperature, where  $T_{sc} = 0.2$  K in the three-dimensional electronic state of  $\text{CeIn}_3$  at 2.5 GPa is compared to  $T_{sc} = 2.2$  K in  $\text{CeRhIn}_5$  at 2.4 GPa. Moreover, it is remarkable that the superconducting pressure region  $\Delta P_{sc}$  is wide in the quasi-two-dimensional electronic state:  $\Delta P_{sc} = 0.5$  GPa in  $\text{CeIn}_3$  and  $\Delta P_{sc} = 3.5$  GPa in  $\text{CeRhIn}_5$ .

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#### References

- [1] N.D. Mathur, F.M. Grosche, S.R. Julian, I.R. Walker, D.M. Freye, R.K.W. Haselwimmer, G.G. Lonzarich, *Nature* 394 (1998) 39.
- [2] H. Hegger, C. Petrovic, E.G. Moshopoulou, M.F. Hundley, J.L. Sarrao, Z. Fisk, J.D. Thompson, *Phys. Rev. Lett.* 84 (2000) 4986.
- [3] S. Kawasaki, T. Mito, Y. Kawasaki, H. Kotegawa, G.-Q. Zheng, Y. Kitaoka, H. Shishido, S. Araki, R. Settai, Y. Ōnuki, *J. Phys. Soc. Jpn.* 73 (2004) 1647.
- [4] S. Kawasaki, T. Mito, Y. Kawasaki, G.-Q. Zheng, Y. Kitaoka, D. Aoki, Y. Haga, Y. Ōnuki, *Phys. Rev. Lett.* 91 (2003) 137001.
- [5] T. Ebihara, I. Umehara, A.K. Albessard, K. Satoh, Y. Ōnuki, *Physica B* 186–188 (1993) 123.
- [6] H. Shishido, R. Settai, D. Aoki, S. Ikeda, H. Nakawaki, T. Iizuka, Y. Inada, K. Sugiyama, T. Takeuchi, K. Kindo, T.C. Kobayashi, Y. Haga, H. Harima, Y. Aoki, T. Namiki, H. Sato, Y. Ōnuki, *J. Phys. Soc. Jpn.* 71 (2002) 162.
- [7] T. Yasuda, H. Shishido, T. Ueda, S. Hashimoto, R. Settai, T. Takeuchi, T.D. Matsuda, Y. Haga, Y. Ōnuki, *J. Phys. Soc. Jpn.* 73 (2004) 1657.
- [8] R. Settai, T. Kubo, H. Shishido, T.C. Kobayashi, Y. Ōnuki, *J. Magn. Mater.* 272–276 (2004) 223.
- [9] K. Betsuyaku, H. Harima, *J. Magn. Mater.* 272–276 (2004) 187.
- [10] R. Movshovich, M. Jaime, J.D. Thompson, C. Petrovic, Z. Fisk, P.G. Pagliuso, J.L. Sarrao, *Phys. Rev. Lett.* 86 (2001) 5152.
- [11] T. Muramatsu, N. Tateiwa, T.C. Kobayashi, K. Shimizu, K. Amaya, D. Aoki, H. Shishido, Y. Haga, Y. Ōnuki, *J. Phys. Soc. Jpn.* 70 (2001) 3362.

- [12] H. Shishido, R. Settai, S. Araki, T. Ueda, Y. Inada, T.C. Kobayashi, T. Muramatsu, Y. Haga, Y. Ōnuki, *Phys. Rev. B.* 66 (2002) 214510.
- [13] R. Settai, H. Shishido, S. Ikeda, Y. Murakawa, M. Nakashima, D. Aoki, Y. Haga, H. Harima, Y. Ōnuki, *J. Phys.: Condens. Matter* 13 (2001) L627.
- [14] S. Ikeda, H. Shishido, M. Nakashima, R. Settai, D. Aoki, Y. Haga, H. Harima, Y. Aoki, T. Namiki, H. Sato, Y. Ōnuki, *J. Phys. Soc. Jpn.* 70 (2001) 2248.
- [15] S. Kawasaki, T. Mito, G.-Q. Zheng, C. Thessieu, Y. Kawasaki, K. Ishida, Y. Kitaoka, T. Muramatsu, T.C. Kobayashi, D. Aoki, S. Araki, Y. Haga, R. Settai, Y. Ōnuki, *Phys. Rev. B.* 65 (2001) 020504(R).
- [16] T. Mito, S. Kawasaki, Y. Kawasaki, G.-Q. Zheng, Y. Kitaoka, D. Aoki, Y. Haga, Y. Ōnuki, *Phys. Rev. Lett.* 90 (2003) 077004.
- [17] A. Llobet, J.S. Gardner, E.G. Moshopoulou, J.-M. Mignot, M. Nicklas, W. Bao, N.O. Moreno, P.G. Pagliuso, I.N. Goncharenko, J.L. Sarrao, J.D. Thompson, *Phys. Rev. B.* 69 (2004) 024403.
- [18] E. Bauer, G. Hilscher, H. Michor, Ch. Paul, E.W. Scheidt, A. Griбанov, Yu. Seropegin, H. Noël, M. Sigrist, P. Rogl, *Phys. Rev. Lett.* 92 (2004) 027003.
- [19] Y. Kitaoka, Y. Kawasaki, T. Mito, S. Kawasaki, G.-Q. Zheng, K. Ishida, D. Aoki, Y. Haga, R. Settai, Y. Ōnuki, C. Geil, F. Steglich, *J. Phys. Chem. Solids* 63 (2002) 1141.
- [20] T. Akazawa, H. Hidaka, T. Fujiwara, T.C. Kobayashi, E. Yamamoto, Y. Haga, R. Settai, Y. Ōnuki, *J. Phys.: Condens. Matter* 16 (2004) L29.
- [21] S. Hashimoto, T. Yasuda, T. Kubo, H. Shishido, T. Ueda, R. Settai, T.D. Matsuda, Y. Haga, H. Harima, Y. Ōnuki, *J. Phys.: Condens. Matter* 16 (2004) 287.